

60 V, dual N-channel Trench MOSFET

15 December 2021

**Product data sheet** 

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Logic-level compatible
- · Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

### Table 1. Quick reference data

						-	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage	_		-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	320	mA
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C		-	1	1.6	Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source 1		D <sub>1</sub> D <sub>2</sub>
2	G1	gate 1		
3	D2	drain 2		
4	S2	source 2		
5	G2	gate 2	1 2 3	
6	D1	drain 1	TSSOP6 (SOT363)	S <sub>1</sub> G <sub>1</sub> S <sub>2</sub> G <sub>2</sub> msd901

## 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
2N7002HS	TSSOP6	plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363				

### 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
2N7002HS	C7%

[1] % = placeholder for manufacturing site code

### 8. Limiting values

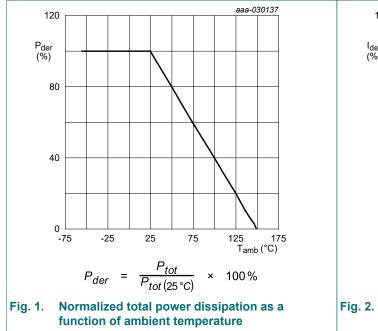
#### Table 5. Limiting values

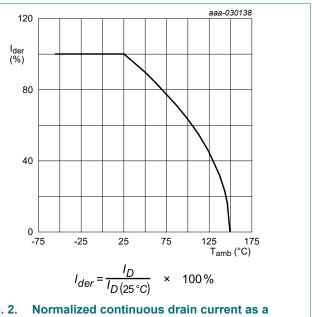
In accordance with the Absolute Maximum Rating System (IEC 60134).

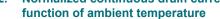
Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or		I			
V <sub>DS</sub>	drain-source voltage	T <sub>amb</sub> = 25 °C		-	60	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	320	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	200	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	1.2	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	960	mW
Per device				I		_
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	420	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode	-				
ls	source current	T <sub>amb</sub> = 25 °C	[1]	-	320	mA

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

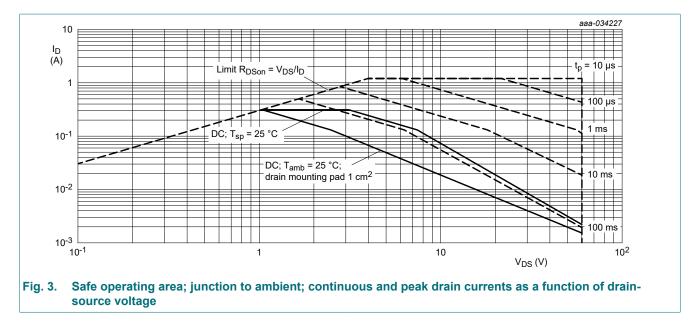
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.







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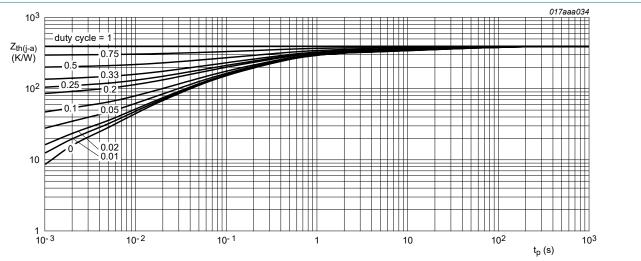
### 9. Thermal characteristics

### Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device							
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	300	K/W
Per transisto	r			<b>I</b>			
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	390	445	K/W
			[2]	-	340	390	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	130	K/W

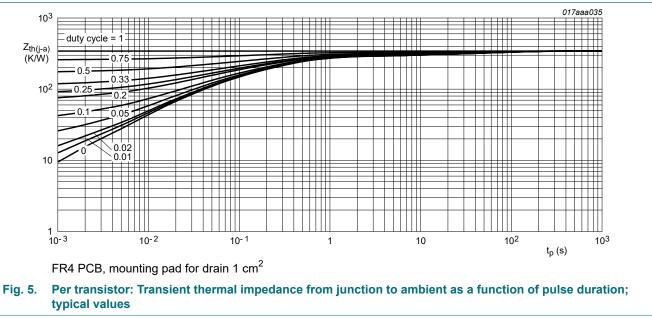
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



FR4 PCB, standard footprint

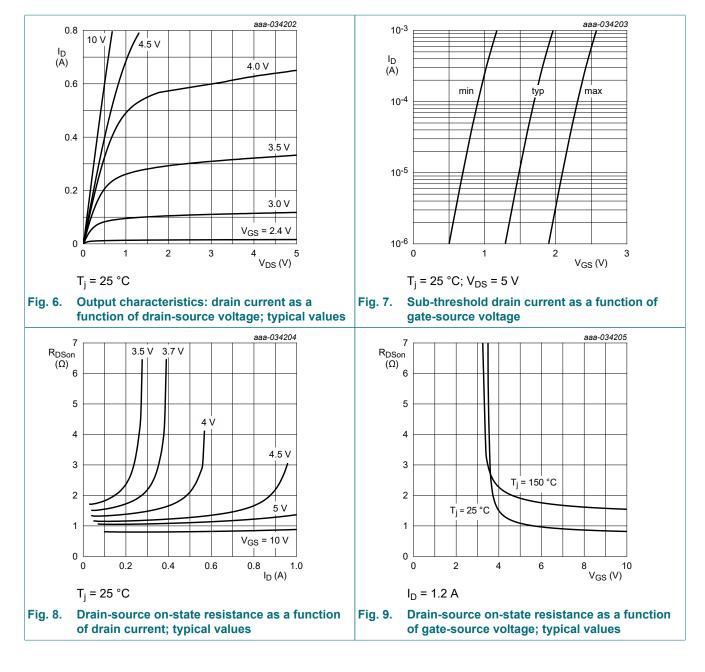




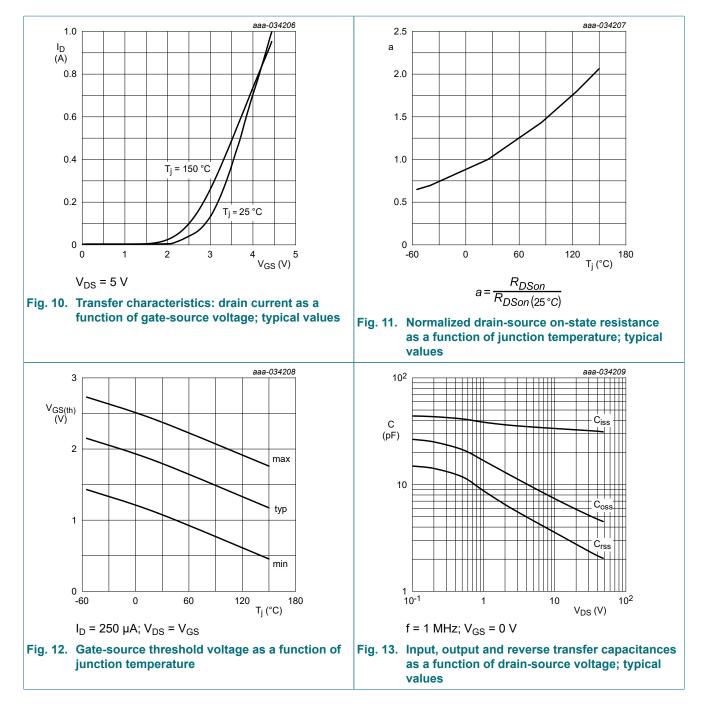
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 10 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	60	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1.1	1.75	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C	-	1	1.6	Ω
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 150 °C	-	2.1	3.3	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 50 mA; T <sub>j</sub> = 25 °C	-	1.3	2	Ω
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	400	-	mS
Dynamic ch	aracteristics	1				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 300 mA; V <sub>GS</sub> = 4.5 V;	-	0.3	0.5	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	34	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; R <sub>L</sub> = 250 Ω; V <sub>GS</sub> = 10 V;	-	2	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	3	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 –	-	6	-	ns
t <sub>f</sub>	fall time	1	-	4	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 115 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	0.47	0.75	1.1	V

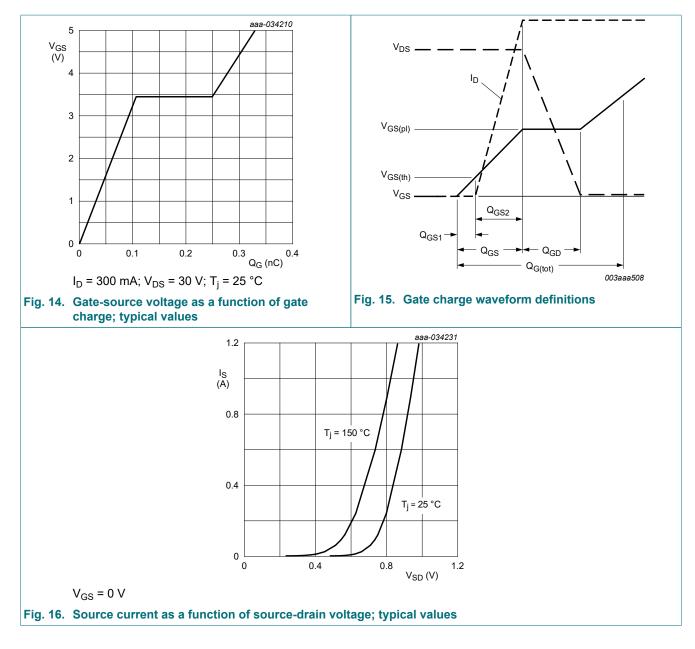
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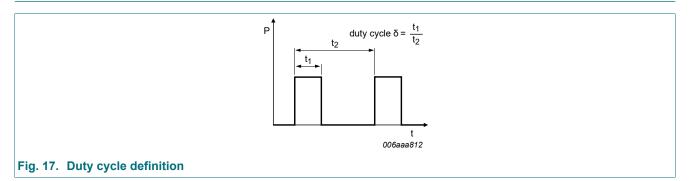
#### 60 V, dual N-channel Trench MOSFET



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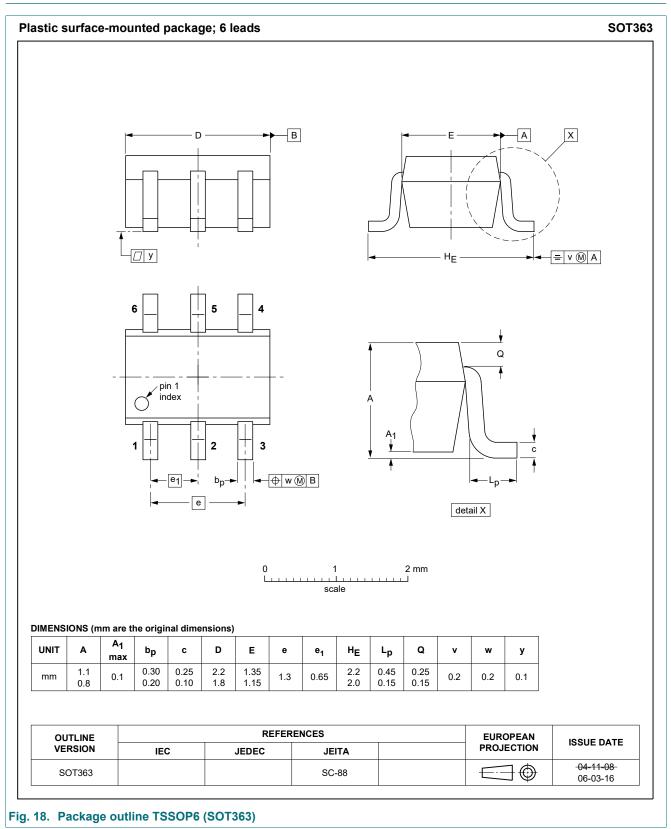
### **11. Test information**



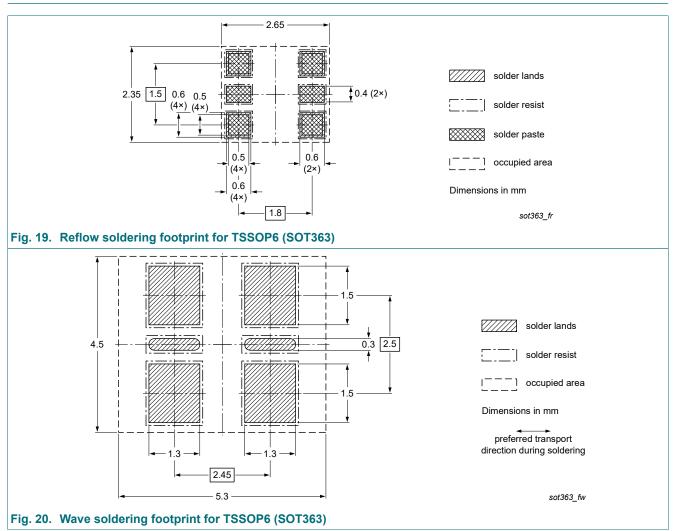
### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



### 13. Soldering



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# 14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
2N7002HS v.3	20211215	Product data sheet	-	2N7002HS v.2		
Modifications:	Changed values	Changed values for parameters $I_D$ and $I_S$				
2N7002HS v.2	20211201	Product data sheet	-	2N7002HS v.1		
2N7002HS v.1	20211119	Preliminary data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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